



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Absolute maximum ratings

($T_a=25^\circ\text{C}$)

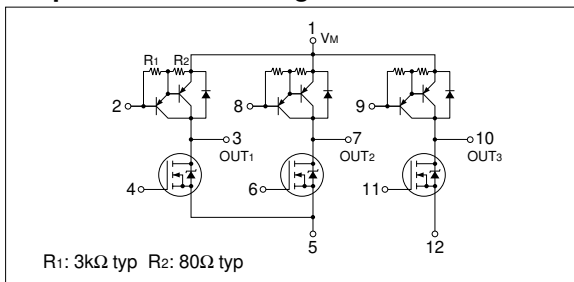
Symbol	Ratings	Unit
V_M	60	V
I_o	± 6 ($PW \leq 100\text{ms}$)	A
I_{OP}	± 10 ($PW \leq 1\text{ms}$)	A
V_{GSS}	± 10	V
I_B	-0.5	A
P_T	5 ($T_a=25^\circ\text{C}$)	W
	35 ($T_c=25^\circ\text{C}$)	
θ_{j-a}	25	$^\circ\text{C/W}$
θ_{j-c}	3.57	$^\circ\text{C/W}$
V_{ISO}	1000 (Between fin and lead pin, AC)	V_{rms}
T_j	150	$^\circ\text{C}$
T_{stg}	-40 to +150	$^\circ\text{C}$

Electrical characteristics (Sink : N channel MOSFET)

($T_a=25^\circ\text{C}$)

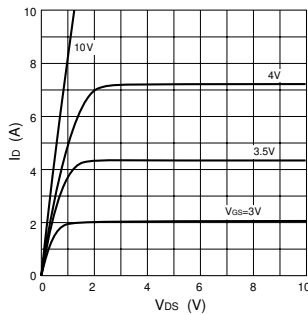
Symbol	Specification			Unit	Conditions
	min	typ	max		
$V_{(BR)DSS}$	60			V	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$
I_{GSS}			± 500	nA	$V_{GS}=\pm 10\text{V}$
I_{DSS}			250	μA	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$
V_{TH}	1.0		2.0	V	$V_{DS}=10\text{V}$, $I_D=250\mu\text{A}$
$R_{DS(ON)}$	3.1	4.6		S	$V_{DS}=10\text{V}$, $I_D=4\text{A}$
		0.17	0.22		$V_{GS}=10\text{V}$, $I_D=4\text{A}$
C_{iss}	400	160		pF	$V_{BS}=25\text{V}$, $f=1.0\text{MHz}$,
					$V_{GS}=0\text{V}$
C_{oss}				pF	$V_{GS}=0\text{V}$
t_{on}		80		ns	$I_D=4\text{A}$, $V_{DD}=30\text{V}$,
t_{off}		50		ns	$V_{GS}=5\text{V}$
V_{SD}		1.1	1.5	V	$I_{SD}=4\text{A}$, $V_{GS}=0\text{V}$
t_{rr}		150		ns	$I_F=\pm 100\text{mA}$

Equivalent circuit diagram

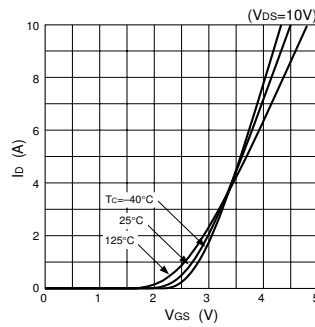


Characteristic curves (N-channel)

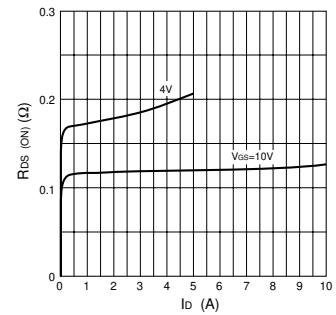
$V_{DS}-I_D$ Characteristics (Typical)



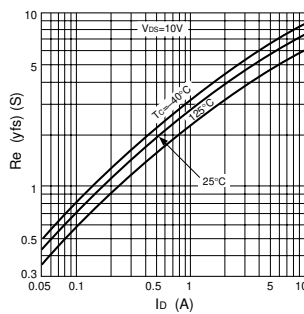
$V_{GS}-I_D$ Temperature Characteristics (Typical)



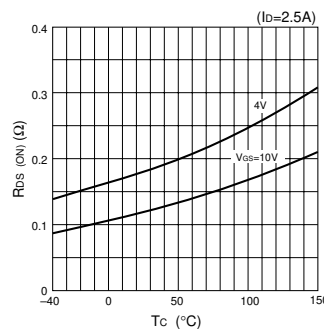
$I_{DS}-R_{DS(ON)}$ Characteristics (Typical)



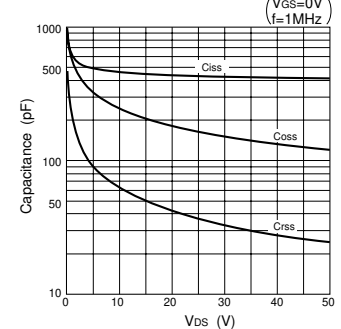
$I_D-Re_{(yfs)}$ Temperature Characteristics (Typical)



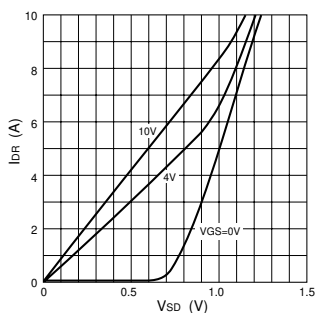
$T_c-R_{DS(ON)}$ Characteristics (Typical)



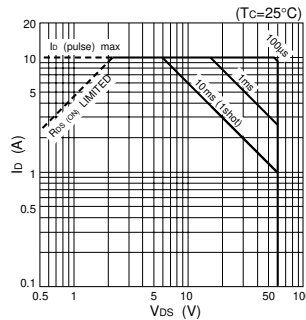
$V_{DS}-C_{pac}$ Characteristics (Typical)



$V_{SD}-I_{DR}$ Characteristics (Typical)



Safe Operating Area (SOA)

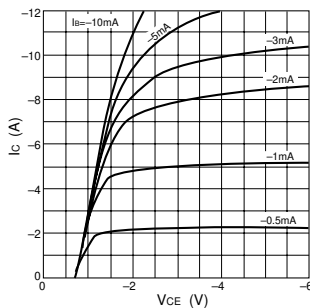


Electrical characteristics (Source: PNP transistor) (T_a=25°C)

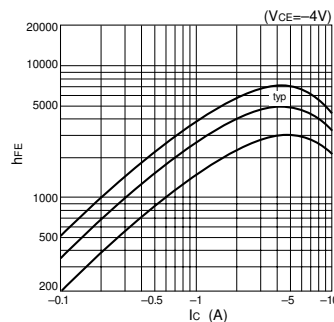
Symbol	Specification			Unit	Conditions
	min	typ	max		
I _{CBO}			-10	μA	V _{CB} = -60V
I _{EBO}	-1		-5	mA	V _{EB} = -6V
V _{CEO}	-60			V	I _C = -25mA
h _{FE}	2000	5000	12000		V _{CE} = -4V, I _C = -4A
V _{CE(sat)}			-1.5	V	I _C = -4A, I _B = -10mA
V _{BE(sat)}			-2.0	V	
V _{FEC}			2.0	V	I _{FEC} = 4A
t _{rr}		1.0		μs	I _F = ±0.5A
t _{on}		1.0		μs	V _{CC} = -25V, I _C = -4A,
t _{stg}		1.4		μs	
t _f		0.6		μs	I _{B1} = -I _{B2} = -10mA
f _T		120		MHz	V _{CE} = -12V, I _E = 1A
C _{ob}		150		pF	V _{CB} = -10V, f = 1MHz

Characteristic curves (PNP)

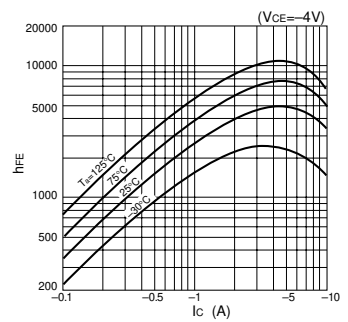
I_C-V_{CE} Characteristics (Typical)



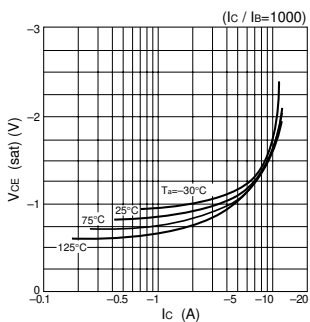
h_{FE}-I_C Characteristics (Typical)



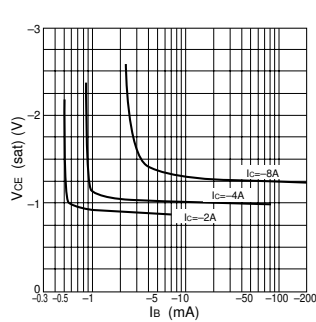
h_{FE}-I_C Temperature Characteristics (Typical)



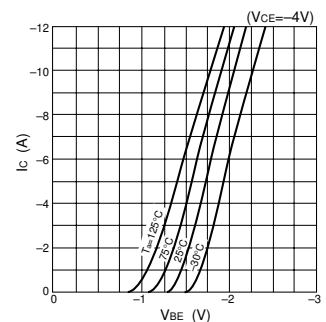
V_{CE(sat)}-I_C Temperature Characteristics (Typical)



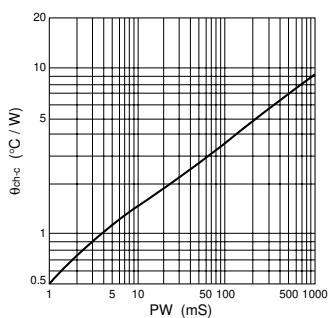
V_{CE(sat)}-I_B Characteristics (Typical)



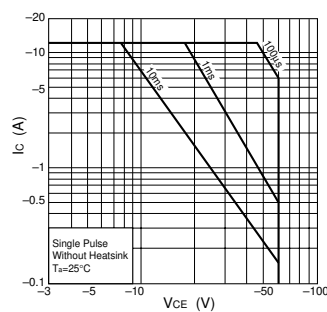
I_C-V_{BE} Temperature Characteristics (Typical)



θ_{j-a}-PW Characteristics



Safe Operating Area (SOA)



P_T-T_a Characteristics

